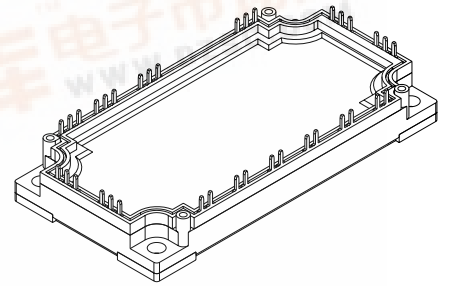
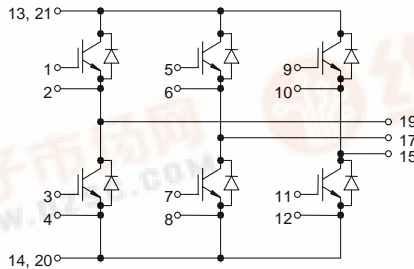


IGBT Modules

Sixpack

Short Circuit SOA Capability
Square RBSOA

$I_{C25} = 170 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.0 \text{ V}$



IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	170	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	115	A
RBSOA	$V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 300$ $V_{CEK} \leq V_{CES}$	A
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	515	W

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

Typical Applications

- AC motor control
- AC servo and robot drives
- power supplies

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 150 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.0 2.3	V V	
$V_{GE(th)}$	$I_C = 3 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.1	1.5 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 150 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega$		125 30 225 35 2.3 4.6	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$	6.5	nF	
Q_{Gon}		$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 150 \text{ A}$	tbd	nC	
R_{thJC}		(per IGBT)		0.24	K/W

